



JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

WBFBP-03D Plastic-Encapsulate Transistors

TK3906LLD03 TRANSISTOR

DESCRIPTION

PNP Epitaxial Silicon Transistor

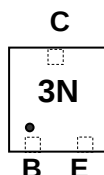
FEATURES

Epitaxial Planar Die Construction
Complementary NPN Type Available (TK3904LLD03)
Ultra-Small Surface Mount Package
Also Available in Lead Free Version

APPLICATION

General Purpose Amplifier, switching
For portable equipment:(i.e. Mobile phone,MP3, MD,CD-ROM,
DVD-ROM, Note book PC, etc.)

MARKING:3N

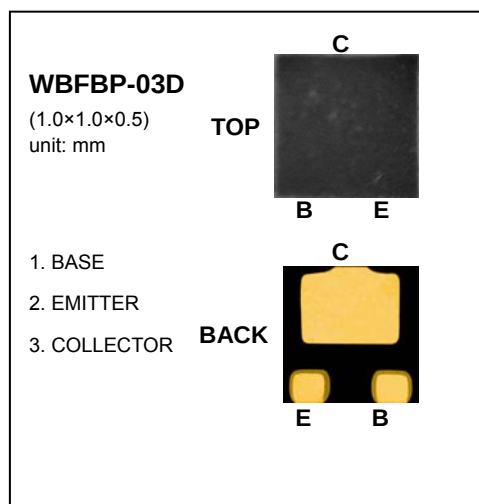


MAXIMUM RATINGS* T_A=25°C unless otherwise noted

Symbol	Parameter	Value	Units
V _{CBO}	Collector-Base Voltage	-40	V
V _{CEO}	Collector-Emitter Voltage	-40	V
V _{EBO}	Emitter-Base Voltage	-5	V
I _C	Collector Current -Continuous	-200	mA
P _D	Power Dissipation	100	mW
R _{θJA}	Thermal Resistance, Junction to Ambient	1250	°C/W
T _J	Operating Temperature	150	°C
T _{stg}	Storage and Temperature	-55-150	°C

ELECTRICAL CHARACTERISTICS (T_A=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	V _{(BR)CBO}	I _C =-10μA, I _E =0	-40			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C =-1mA, I _B =0	-40			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E =-10μA, I _C =0	-5			V
Collector cut-off current	I _{CEX}	V _{CE} =-30V, V _{EB(off)} =-3V			-0.05	μA
Emitter cut-off current	I _{EBO}	V _{EB} =-5V, I _C =0			-0.1	μA
DC current gain	h _{FE(1)}	V _{CE} =-1V, I _C =-0.1mA	60			
	h _{FE(2)}	V _{CE} =-1V, I _C =-1mA	80			
	h _{FE(3)}	V _{CE} =-1V, I _C =-10mA	100		300	
	h _{FE(4)}	V _{CE} =-1V, I _C =-50mA	60			
	h _{FE(5)}	V _{CE} =-1V, I _C =-100mA	30			
Collector-emitter saturation voltage	V _{CE(sat)1}	I _C =-10mA, I _B =-1mA			-0.25	V
	V _{CE(sat)2}	I _C =-50mA, I _B =-5mA			-0.4	V
Base-emitter saturation voltage	V _{BE(sat)1}	I _C =-10mA, I _B =-1mA	-0.65		-0.85	V
	V _{BE(sat)2}	I _C =-50mA, I _B =-5mA			-0.95	V
Transition frequency	f _T	V _{CE} =-20V, I _C =-10mA, f=100MHz	250			MHz



ELECTRICAL CHARACTERISTICS (Ta=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector output capacitance	C_{obo}	$V_{CB}=-5V, I_E=0, f=1MHz$			4.5	pF
Input capacitance	C_{iob}	$V_{EB}=-0.5V, I_C=0, f=1MHz$			10	pF
Noise figure	NF	$V_{CE}=-5V, I_C=0.1mA, f=1KHz, R_S=1K\Omega$			4	dB
Delay time	t_d	$V_{CC}=-3V, V_{BE(OFF)}=0.5V, I_C=-10mA, I_{B1}=-1mA$			35	nS
Rise time	t_r				35	nS
Storage time	t_s	$V_{CC}=-3V, I_C=-10mA, I_{B1}=I_{B2}=-1mA$			225	nS
Fall time	t_f				75	nS

Typical Characteristics

TK3906LLD03

